Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-40	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V_{GS} = -10V	Steady State	T_A = +25°C T_A = +70°C	I_D	-10.3 -8.3	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	-13.7 -11	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	-80	A
Maximum Continuous Body Diode Forward Current (Note 7)			I_S	-2.6	A
Avalanche Current, L = 0.1mH			I_{AS}	-34	A
Avalanche Energy, L = 0.1mH			E_{AS}	58	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 6)		P_D	1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	123	°C/W
	t<10s		69	
Total Power Dissipation (Note 7)		P_D	2.1	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	60	°C/W
	t<10s		34	
Thermal Resistance, Junction to Case (Note 7)		$R_{\theta JC}$	3.3	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-40	—	—	V	V_{GS} = 0V, I_D = -250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	—	—	-1	µA	V_{DS} = -40V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-1	—	-3	V	V_{DS} = V_{GS}, I_D = -250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	9.4	13	mΩ	V_{GS} = -10V, I_D = -10A
		—	12.3	18		V_{GS} = -4.5V, I_D = -8A
Diode Forward Voltage	V_{SD}	—	-0.7	-1.2	V	V_{GS} = 0V, I_S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	3,426	—	pF	V_{DS} = -20V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	283	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	235	—	pF	
Gate Resistance	R_g	—	4.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = -4.5V)	Q_g	—	32.5	—	nC	V_{DS} = -20V, I_D = -10A
Total Gate Charge (V_{GS} = -10V)	Q_g	—	68.6	—	nC	
Gate-Source Charge	Q_{gs}	—	8.2	—	nC	
Gate-Drain Charge	Q_{gd}	—	9.9	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.3	—	ns	V_{DD} = -20V, V_{GEN} = -10V, R_G = 3Ω, I_D = -10A
Turn-On Rise Time	t_R	—	20	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	126	—	ns	
Turn-Off Fall Time	t_F	—	83	—	ns	
Body Diode Reverse Recovery Time	t_{RR}	—	19.5	—	ns	I_F = -10A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	9.8	—	nC	

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

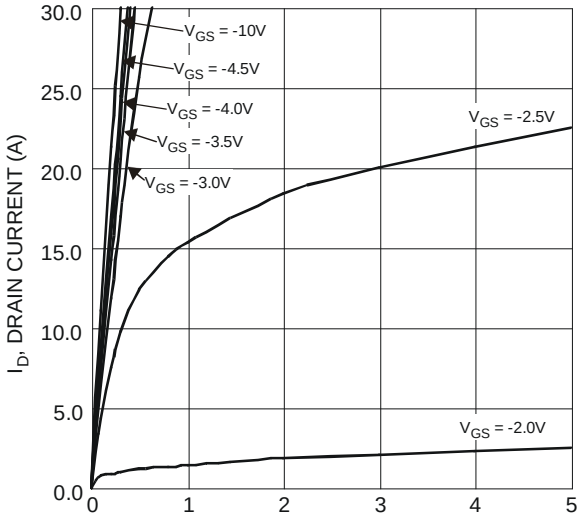


Figure 1 Typical Output Characteristics

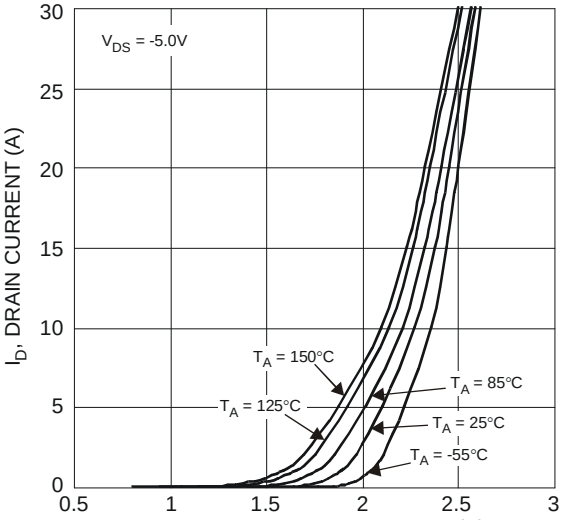


Figure 2 Typical Transfer Characteristics

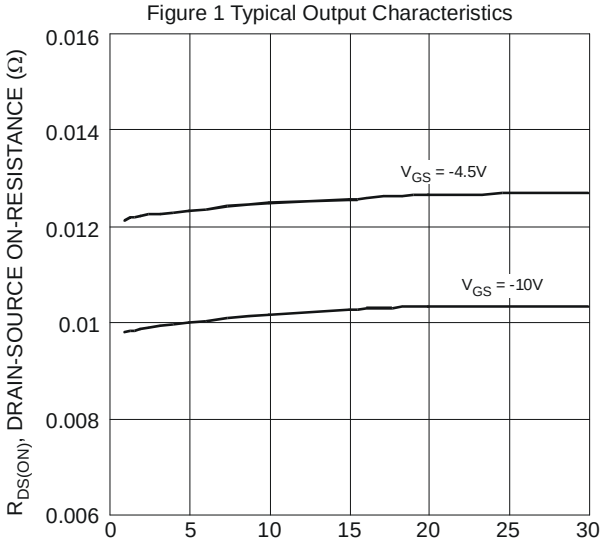


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

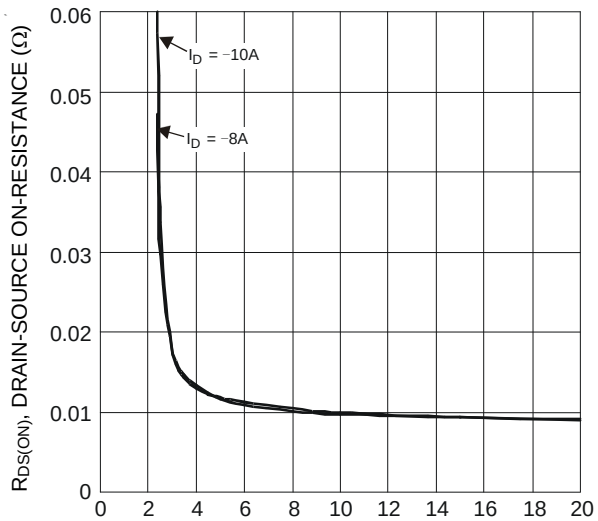


Figure 4 Typical Transfer Characteristics

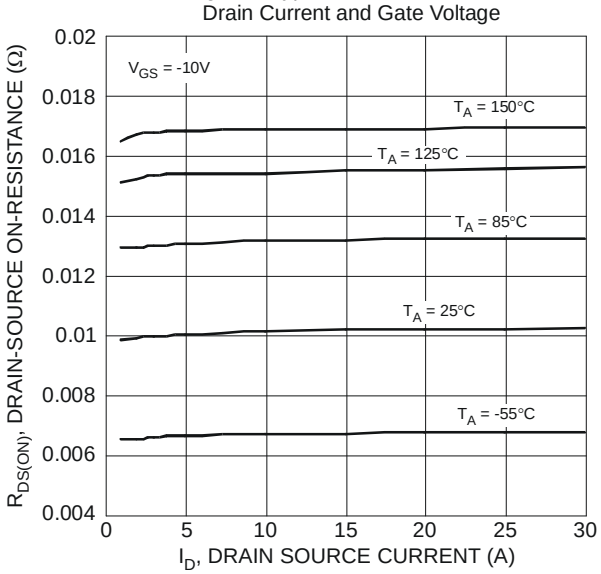


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

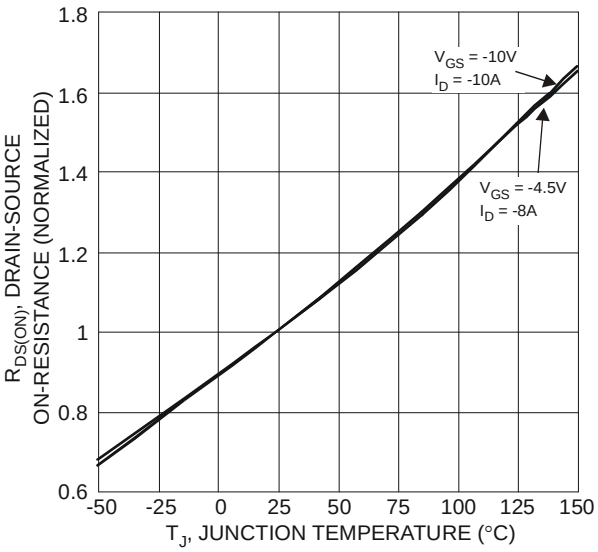


Figure 6 On-Resistance Variation with Temperature

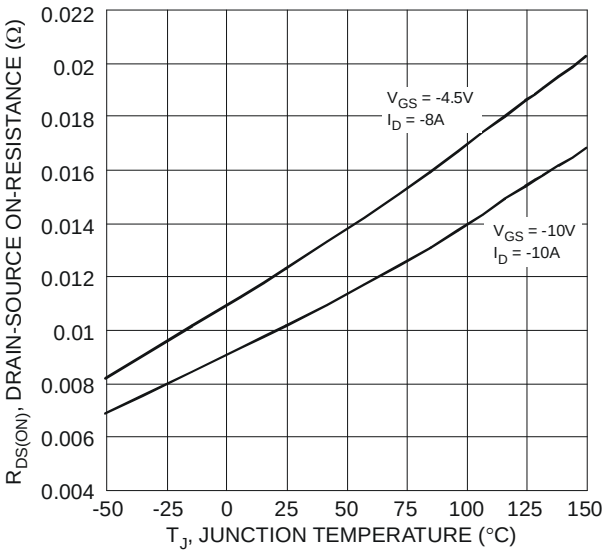


Figure 7 On-Resistance Variation with Temperature

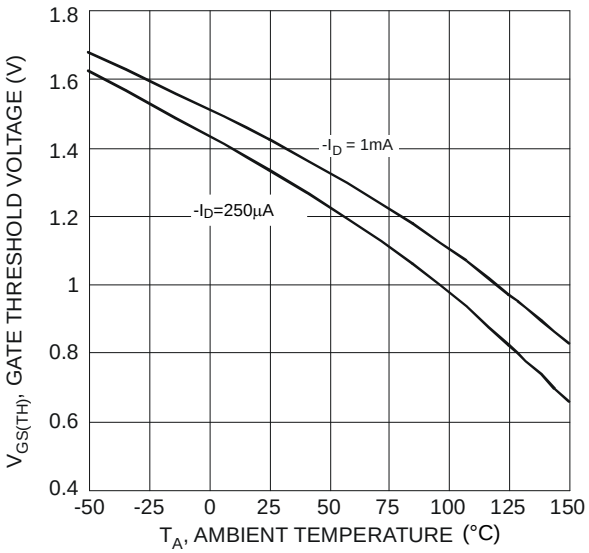


Figure 8 Gate Threshold Variation vs. Ambient Temperature

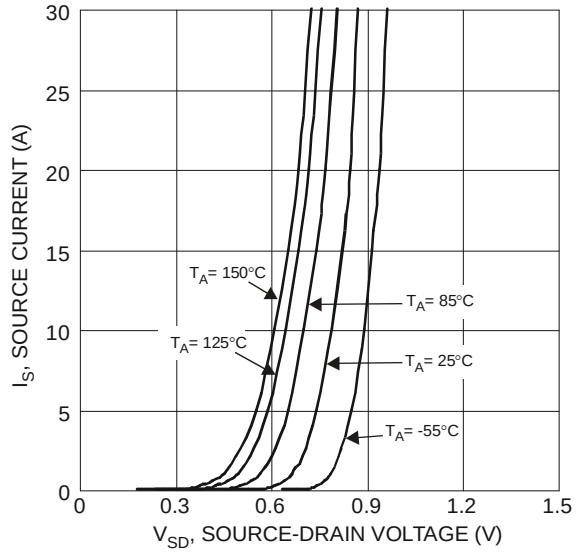


Figure 9 Diode Forward Voltage vs. Current

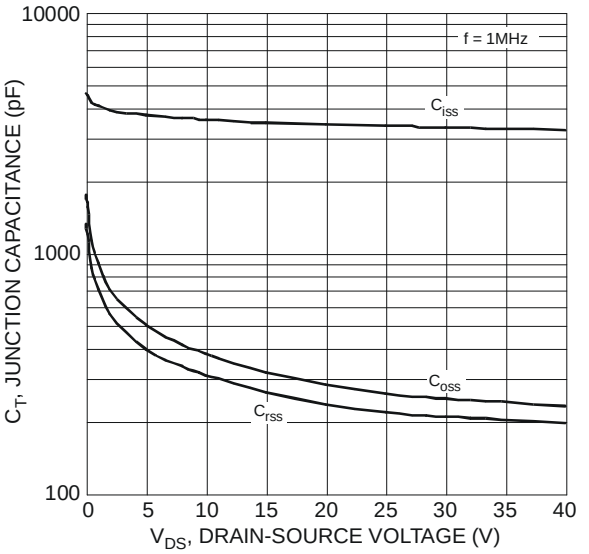


Figure 10 Typical Junction Capacitance

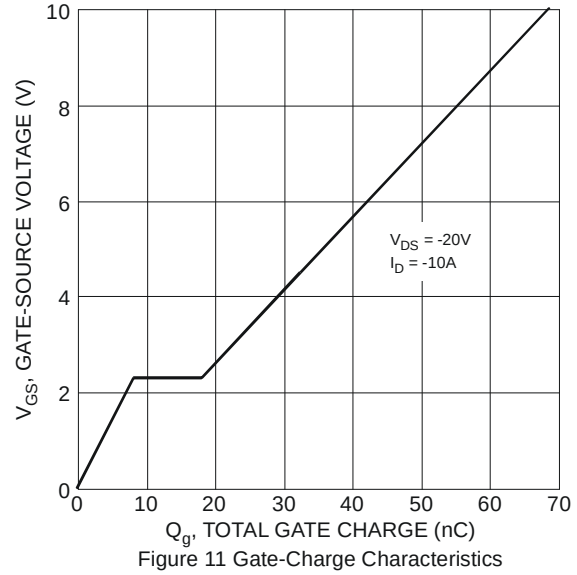


Figure 11 Gate-Charge Characteristics

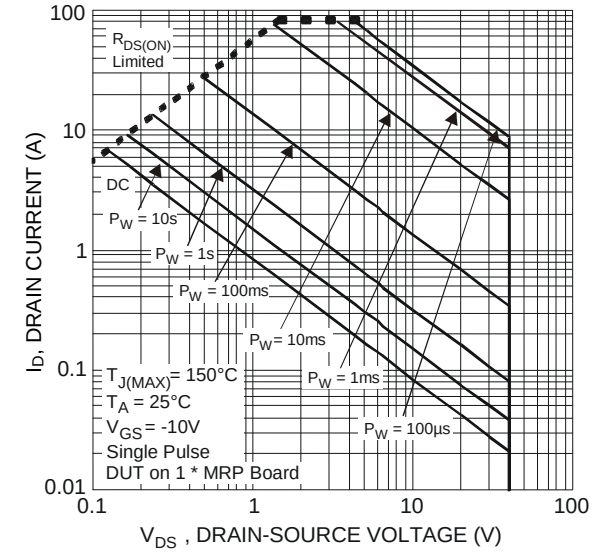


Figure 12 SOA, Safe Operation Area

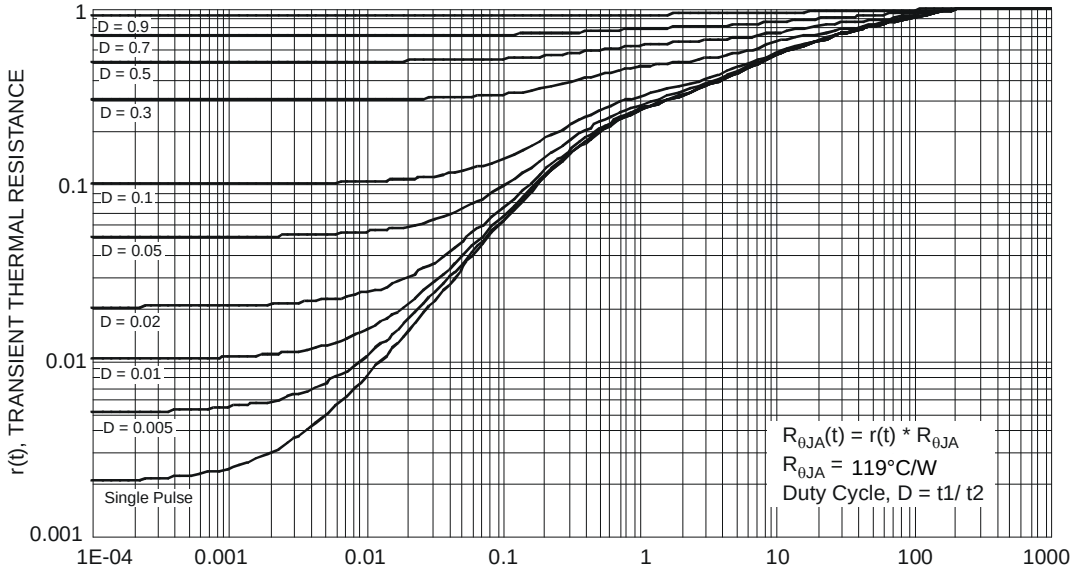
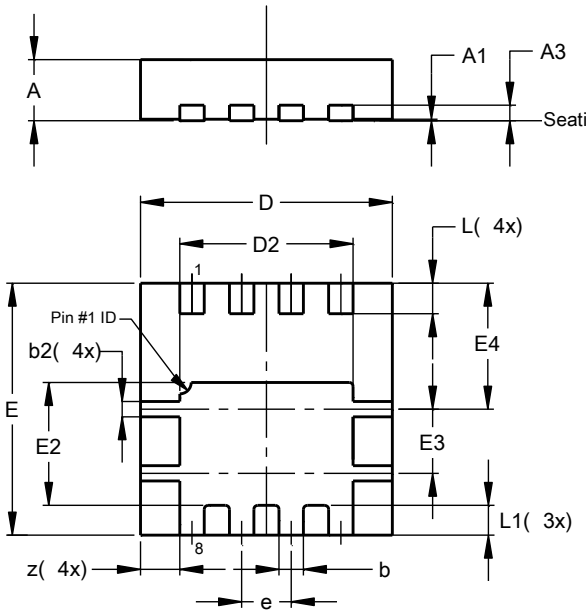


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

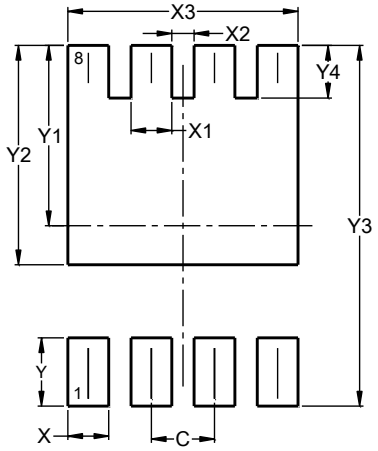


PowerDI3333-8			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3 25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	–	–	0.65
L	0.35	0.45	0.40
L1	–	–	0.39
z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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